

EconoPIM™3 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 200\text{ A} / I_{CRM} = 400\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Overload operation up to 175°C
 - Low $V_{CE,sat}$
- Mechanical features
 - Integrated NTC temperature sensor
 - Solder contact technology
 - Copper base plate
 - Al_2O_3 substrate with low thermal resistance



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

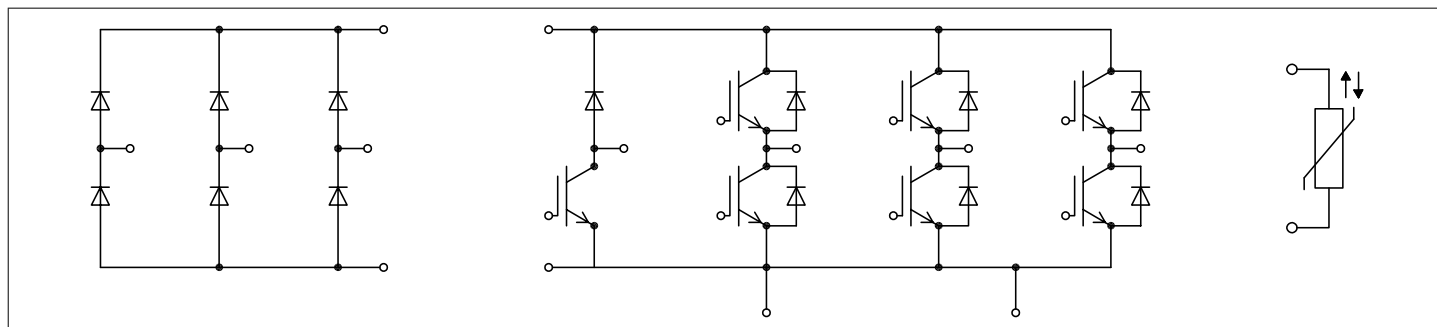


Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	Diode, Rectifier	6
5	IGBT, Brake-Chopper	7
6	Diode, Brake-Chopper	9
7	NTC-Thermistor	10
8	Characteristics diagrams	11
9	Circuit diagram	17
10	Package outlines	18
11	Module label code	19
	Revision history	20
	Disclaimer	21

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			25		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$, per switch		1.1		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		1.6		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	G			300		g

Note: The current under continuous operation is limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \max} = 175^\circ\text{C}$ $T_C = 70^\circ\text{C}$	200	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	400	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	V_{GETh}	$I_C = 4.6\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V$			3.34		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0.75		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			40.3		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.14		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.02	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 200\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.203		μs
			$T_{vj} = 125\ ^\circ C$		0.226		
			$T_{vj} = 175\ ^\circ C$		0.239		
Rise time (inductive load)	t_r	$I_C = 200\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.094		μs
			$T_{vj} = 125\ ^\circ C$		0.097		
			$T_{vj} = 175\ ^\circ C$		0.099		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 200\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.351		μs
			$T_{vj} = 125\ ^\circ C$		0.414		
			$T_{vj} = 175\ ^\circ C$		0.433		
Fall time (inductive load)	t_f	$I_C = 200\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.103		μs
			$T_{vj} = 125\ ^\circ C$		0.198		
			$T_{vj} = 175\ ^\circ C$		0.262		
Turn-on energy loss per pulse	E_{on}	$I_C = 200\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 2.7\ \Omega, di/dt = 2050\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		25.1		mJ
			$T_{vj} = 125\ ^\circ C$		38.3		
			$T_{vj} = 175\ ^\circ C$		45.9		
Turn-off energy loss per pulse	E_{off}	$I_C = 200\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 2.7\ \Omega, dv/dt = 3250\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		12.9		mJ
			$T_{vj} = 125\ ^\circ C$		20.5		
			$T_{vj} = 175\ ^\circ C$		23.8		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$		640		A
				600		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.231	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m} \cdot \text{K)}$		0.0670		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	°C

Note: $T_{vj op} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		200	A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	400	A
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	A^2s
			$T_{vj} = 175^\circ\text{C}$	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$	1.72	2.10	V
			$T_{vj} = 125^\circ\text{C}$	1.59		
			$T_{vj} = 175^\circ\text{C}$	1.52		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 2050 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	79.6		A
			$T_{vj} = 125^\circ\text{C}$	105		
			$T_{vj} = 175^\circ\text{C}$	118		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}$, $I_F = 200 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 2050 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	15.7		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$	27.7		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	35.6		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}$, $I_F = 200 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 2050 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	4.85		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	9.64		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	12.2		
Thermal resistance, junction to case	R_{thJC}	per diode			0.376	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.0730		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1600	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_C = 110 \text{ }^\circ\text{C}$	150	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_C = 110 \text{ }^\circ\text{C}$	150	A
Surge forward current	I_{FSM}	$t_P = 10 \text{ ms}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	A
			$T_{vj} = 150 \text{ }^\circ\text{C}$	
I^2t - value	I^2t	$t_P = 10 \text{ ms}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	A^2s
			$T_{vj} = 150 \text{ }^\circ\text{C}$	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 200 \text{ A}$		1.02		V
Reverse current	I_r	$T_{vj} = 150 \text{ }^\circ\text{C}$, $V_R = 1600 \text{ V}$		1.4		mA

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			0.278	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$		0.0690		K/W
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj max} = 175 \text{ °C}$	$T_C = 75 \text{ °C}$	150	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj op}$		300	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE sat}$	$I_C = 150 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ °C}$		1.55	1.80	V
			$T_{vj} = 125 \text{ °C}$		1.69		
			$T_{vj} = 175 \text{ °C}$		1.77		
Gate threshold voltage	V_{GEth}	$I_C = 3.5 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25 \text{ °C}$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}$			2.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25 \text{ °C}$			1		Ω
Input capacitance	C_{ies}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$			30.1		nF
Reverse transfer capacitance	C_{res}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$			0.105		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$			0.005	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25 \text{ °C}$				100	nA

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	t_{don}	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5.6\ \Omega$	$T_{vj} = 25\text{ °C}$	0.197		μs
			$T_{vj} = 125\text{ °C}$	0.208		
			$T_{vj} = 175\text{ °C}$	0.215		
Rise time (inductive load)	t_r	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5.6\ \Omega$	$T_{vj} = 25\text{ °C}$	0.085		μs
			$T_{vj} = 125\text{ °C}$	0.090		
			$T_{vj} = 175\text{ °C}$	0.093		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\text{ °C}$	0.419		μs
			$T_{vj} = 125\text{ °C}$	0.502		
			$T_{vj} = 175\text{ °C}$	0.521		
Fall time (inductive load)	t_f	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\text{ °C}$	0.113		μs
			$T_{vj} = 125\text{ °C}$	0.208		
			$T_{vj} = 175\text{ °C}$	0.272		
Turn-on energy loss per pulse	E_{on}	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5.6\ \Omega$, $di/dt =$ $1150\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	12.2		mJ
			$T_{vj} = 125\text{ °C}$	19.1		
			$T_{vj} = 175\text{ °C}$	23.1		
Turn-off energy loss per pulse	E_{off}	$I_C = 150\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 5.6\ \Omega$, $dv/dt =$ $3100\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	10.5		mJ
			$T_{vj} = 125\text{ °C}$	16.1		
			$T_{vj} = 175\text{ °C}$	20.1		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 800\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 8\ \mu\text{s}$, $T_{vj} = 150\text{ °C}$	480		A
			$t_p \leq 7\ \mu\text{s}$, $T_{vj} = 175\text{ °C}$	450		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.290	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m} \cdot \text{K})$		0.0700		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC forward current	I_F			75	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		150	A
I^2t - value	I^2t	$t_P = 10\text{ ms}, V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	450	A^2s
			$T_{vj} = 175\text{ °C}$	370	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 75\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.72	2.10	V
			$T_{vj} = 125\text{ °C}$	1.59		
			$T_{vj} = 175\text{ °C}$	1.52		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600\text{ V}, I_F = 75\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1050\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	51.8		A
			$T_{vj} = 125\text{ °C}$	69.2		
			$T_{vj} = 175\text{ °C}$	79.6		
Recovered charge	Q_r	$V_{CC} = 600\text{ V}, I_F = 75\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1050\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	6.62		μC
			$T_{vj} = 125\text{ °C}$	13.9		
			$T_{vj} = 175\text{ °C}$	19		
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}, I_F = 75\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1050\text{ A}/\mu s (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	1.62		mJ
			$T_{vj} = 125\text{ °C}$	3.39		
			$T_{vj} = 175\text{ °C}$	4.65		
Thermal resistance, junction to case	R_{thJC}	per diode			0.728	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(m \cdot K)$		0.0870		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}, R_{100} = 493\text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

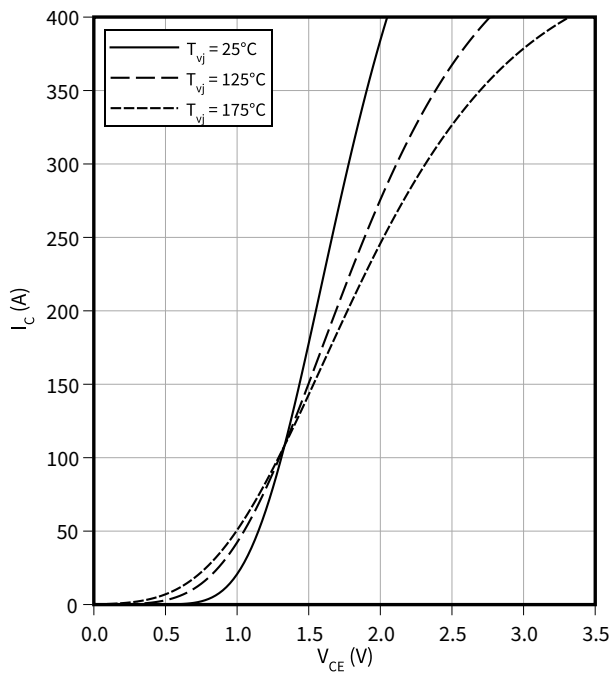
Note: Specification according to the valid application note.

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

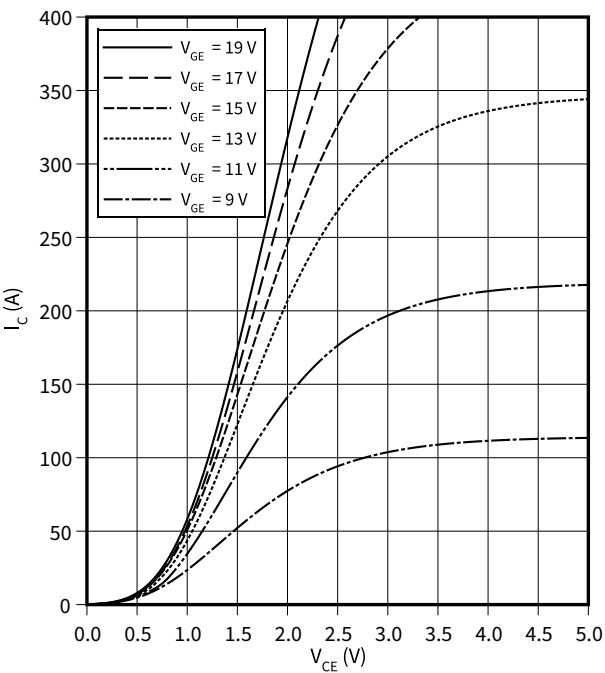
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

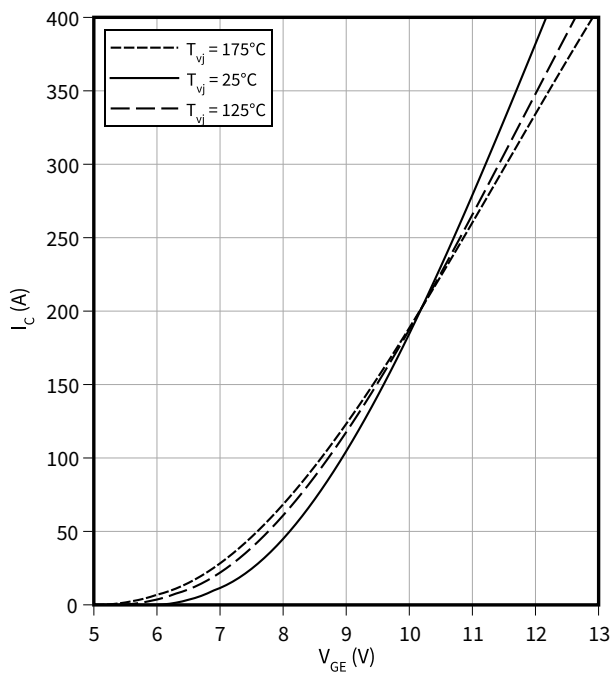
$T_{vj} = 175^\circ\text{C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

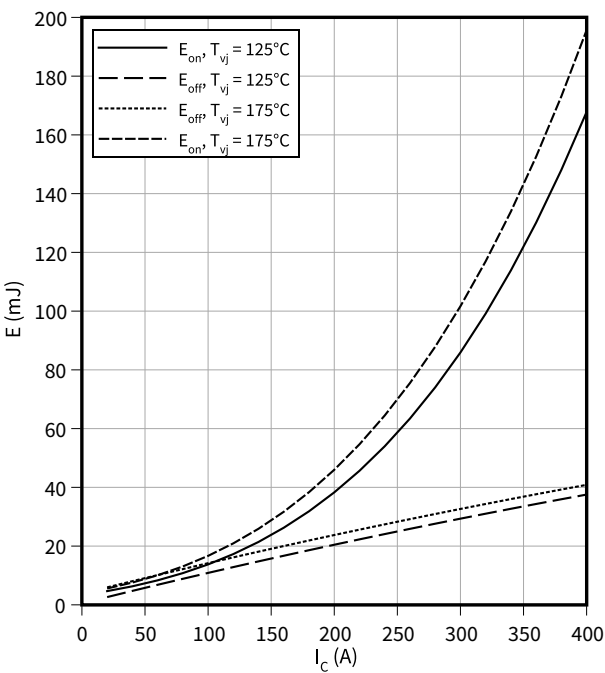
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

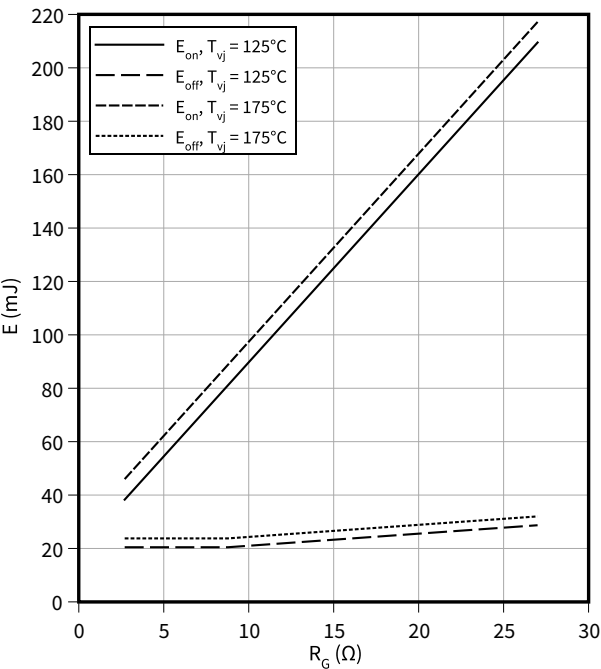
$R_{Goff} = 2.7\ \Omega$, $R_{Gon} = 2.7\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 600\text{ V}$



8 Characteristics diagrams

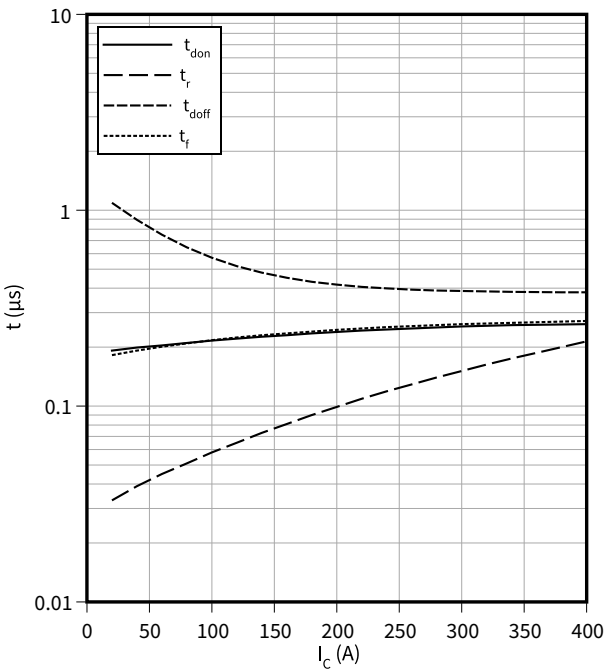
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 200\text{ A}$, $V_{CC} = 600\text{ V}$



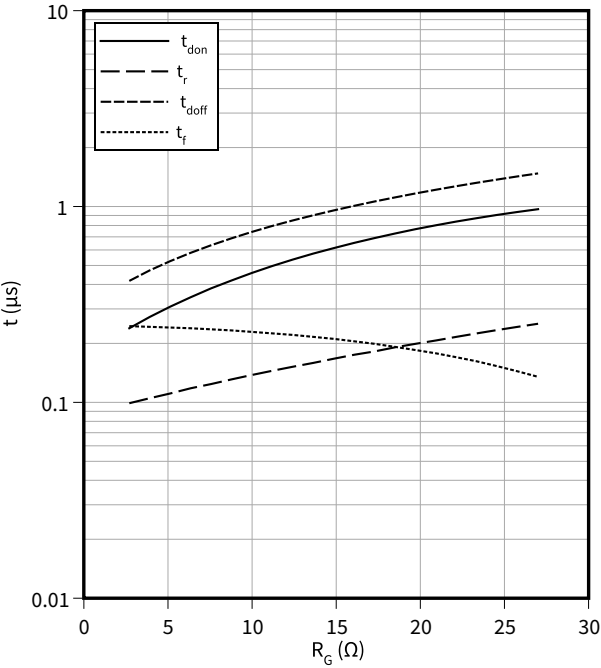
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 2.7\text{ }\Omega$, $R_{Gon} = 2.7\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 600\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



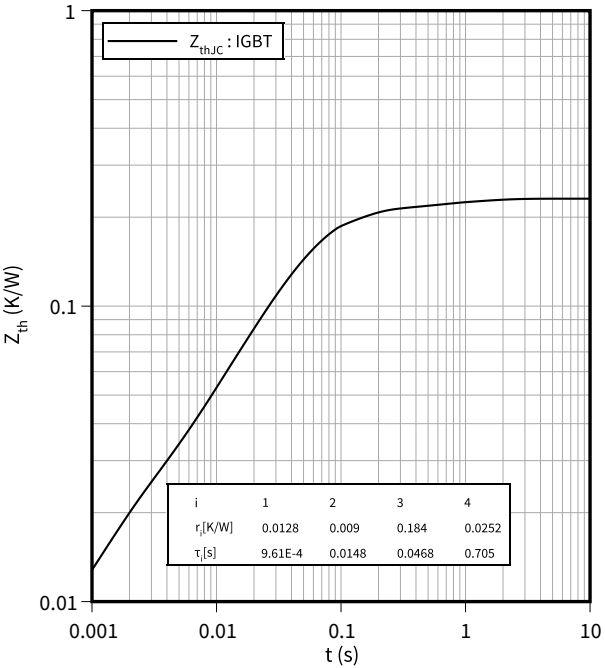
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $I_C = 200\text{ A}$, $V_{CC} = 600\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GE} = \pm 15\text{ V}$



Transient thermal impedance , IGBT, Inverter

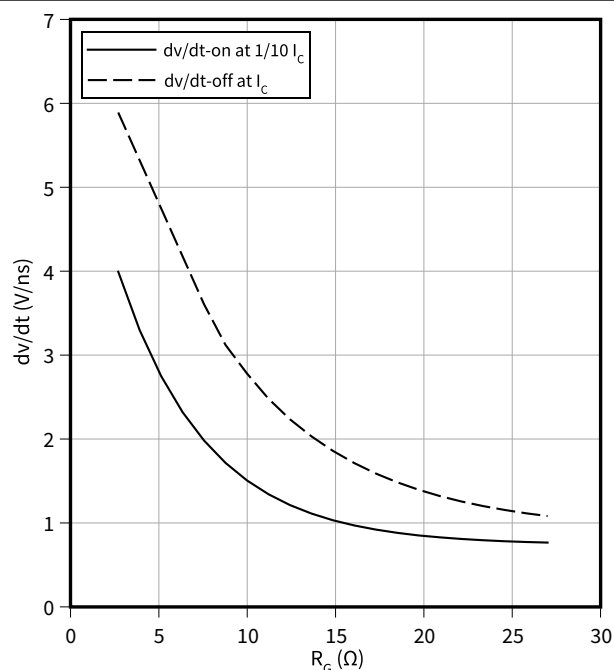
$Z_{th} = f(t)$



Voltage slope (typical), IGBT, Inverter

$$dv/dt = f(R_G)$$

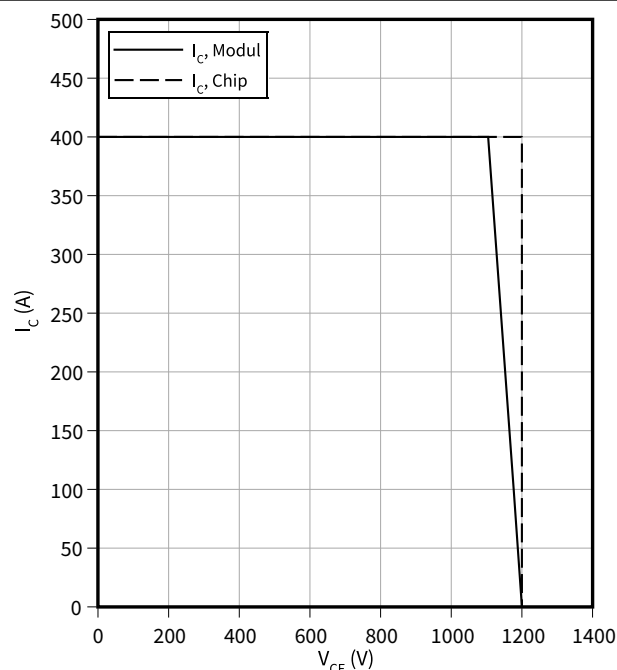
$I_C = 200 \text{ A}$, $V_{CC} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$$I_C = f(V_{CE})$$

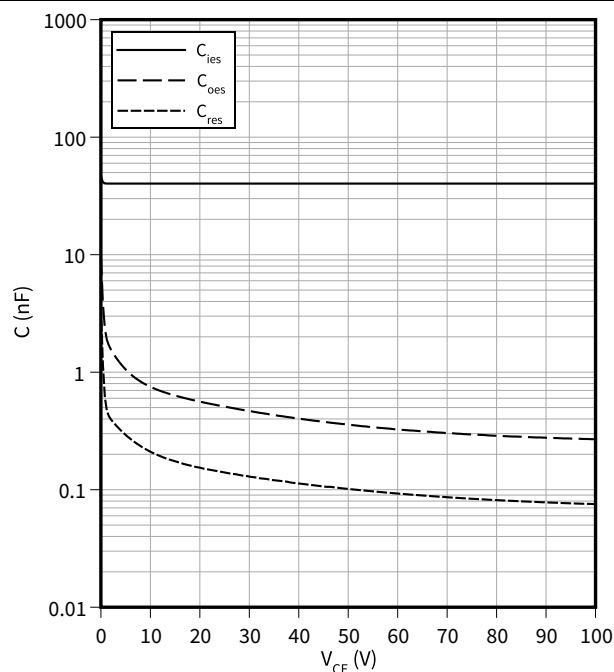
$R_{Goff} = 2.7 \text{ } \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$



Capacity characteristic (typical), IGBT, Inverter

$$C = f(V_{CE})$$

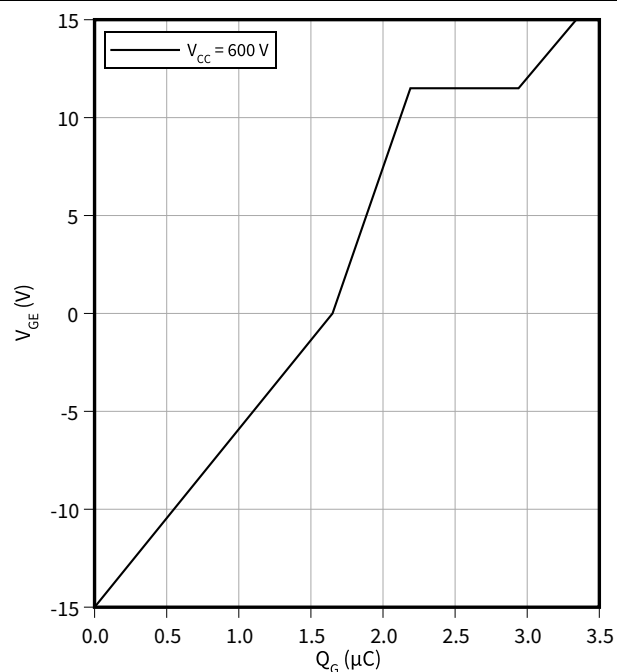
$f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Gate charge characteristic (typical), IGBT, Inverter

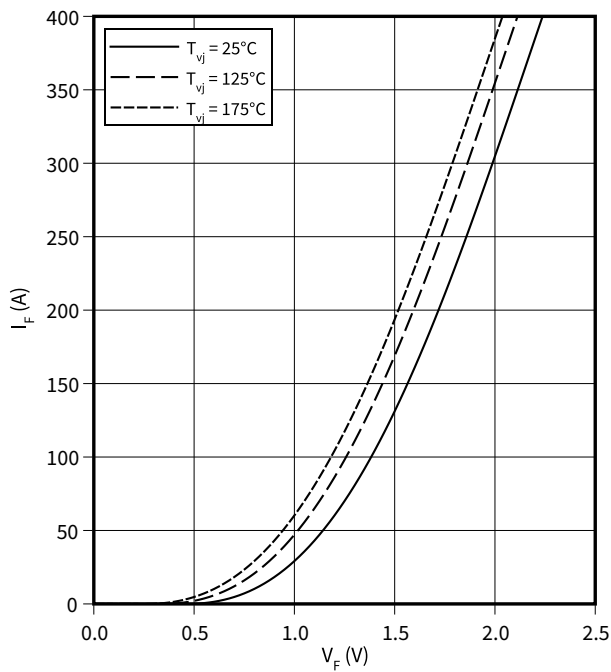
$$V_{GE} = f(Q_G)$$

$I_C = 200 \text{ A}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



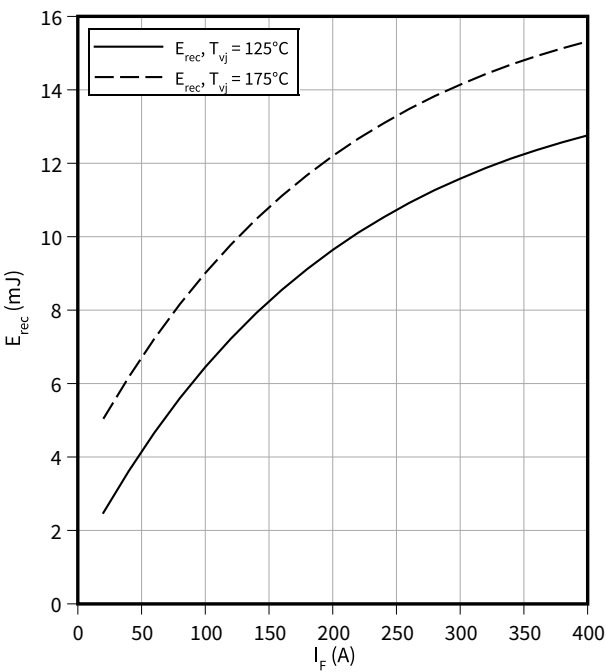
Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$



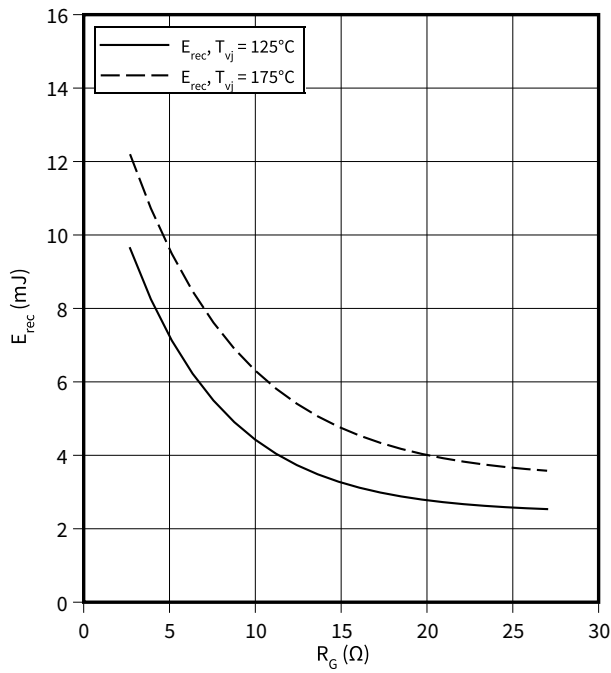
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = 2.7\ \Omega, V_{CC} = 600\ \text{V}$



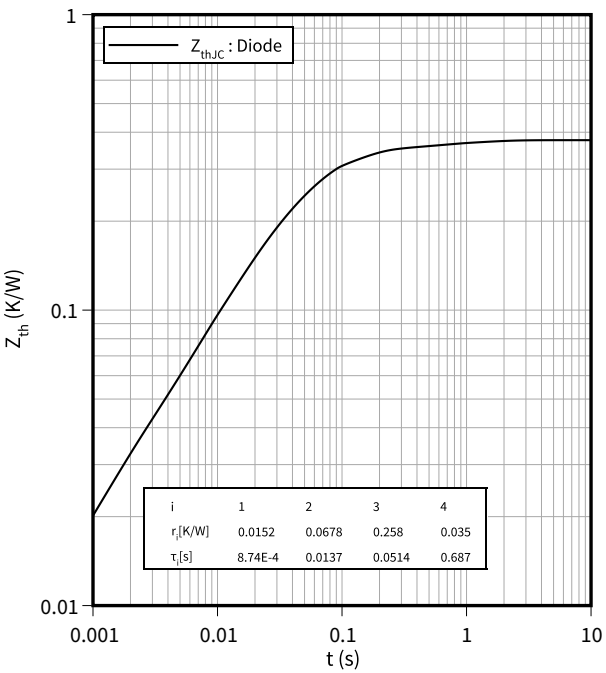
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 200\ \text{A}, V_{CC} = 600\ \text{V}$



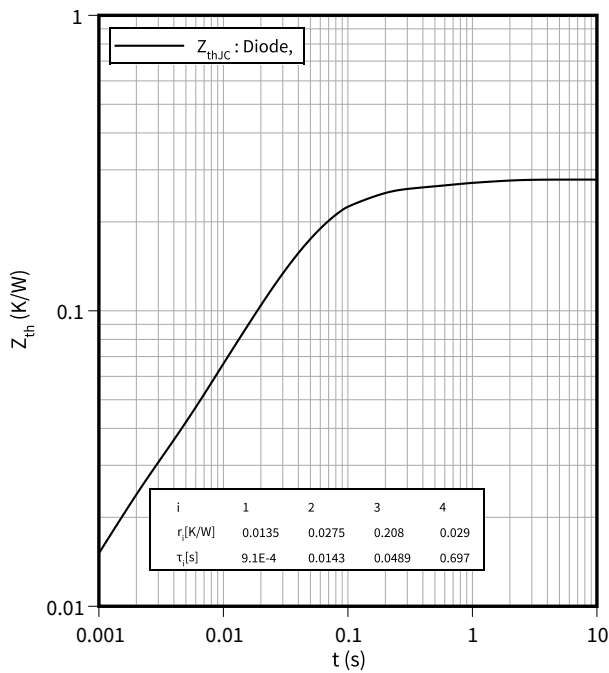
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



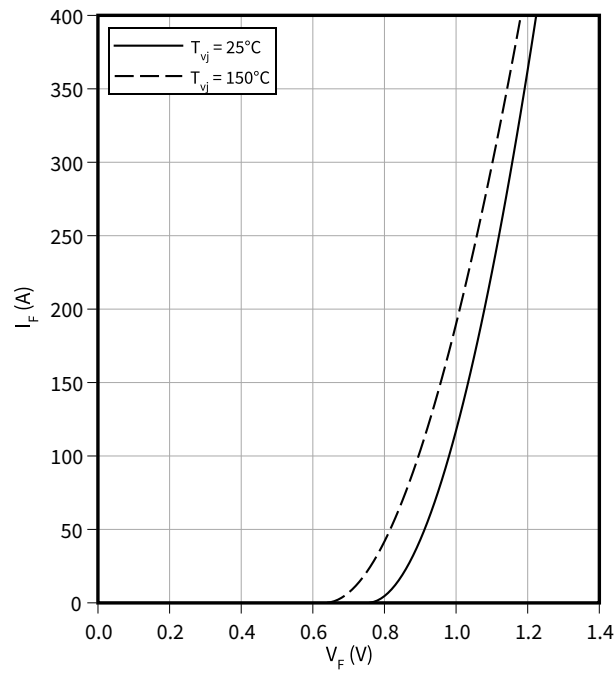
Transient thermal impedance, Diode, Rectifier

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Rectifier

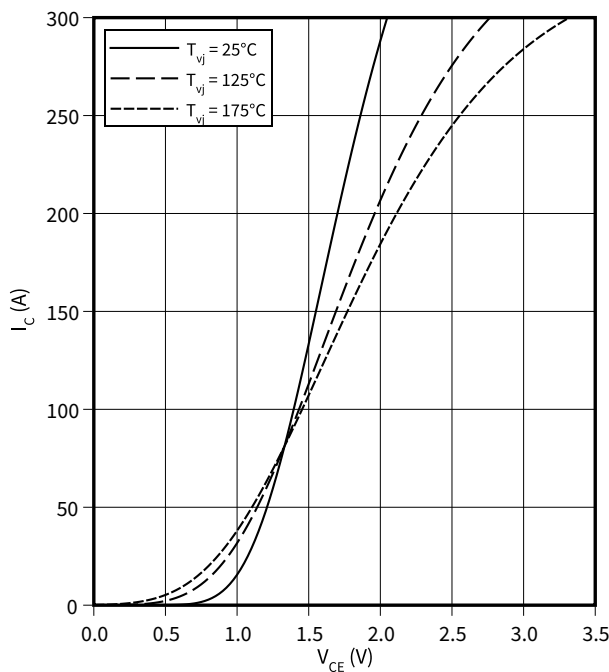
$I_F = f(V_F)$



Output characteristic (typical), IGBT, Brake-Chopper

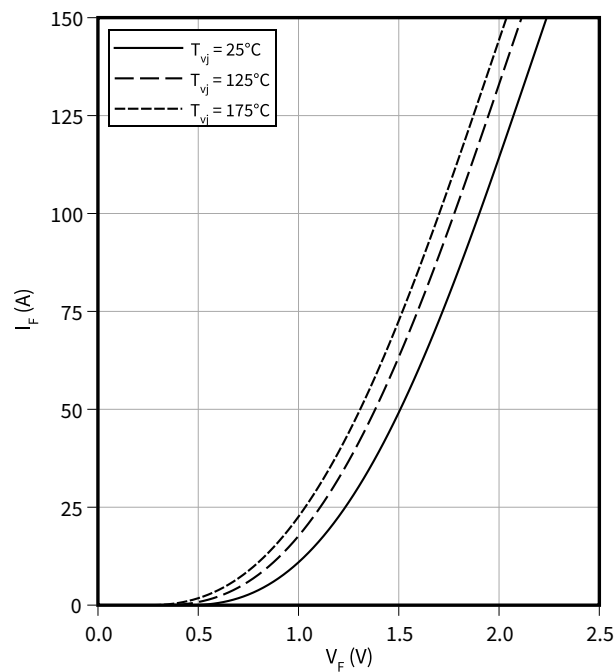
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



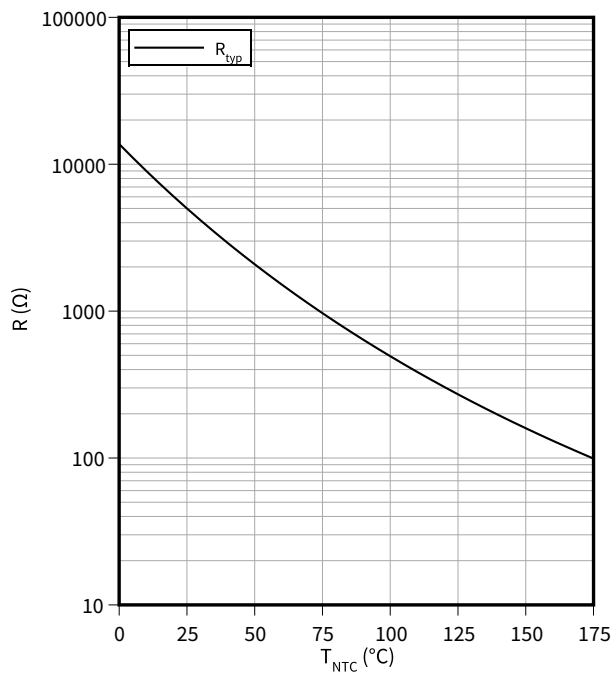
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 **Circuit diagram**

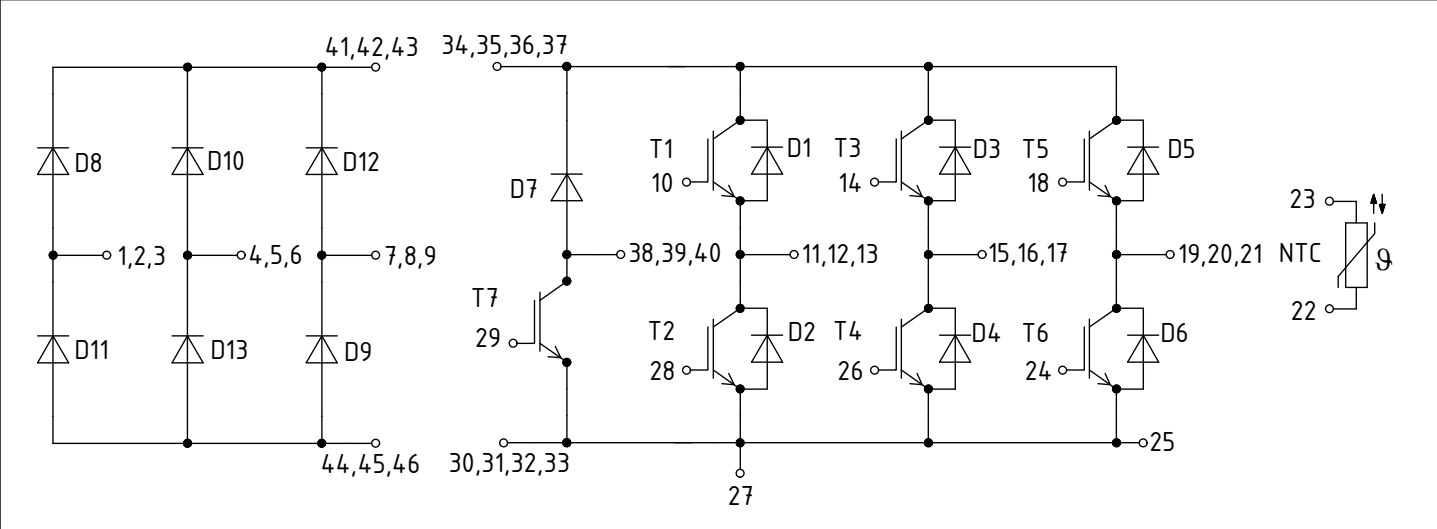
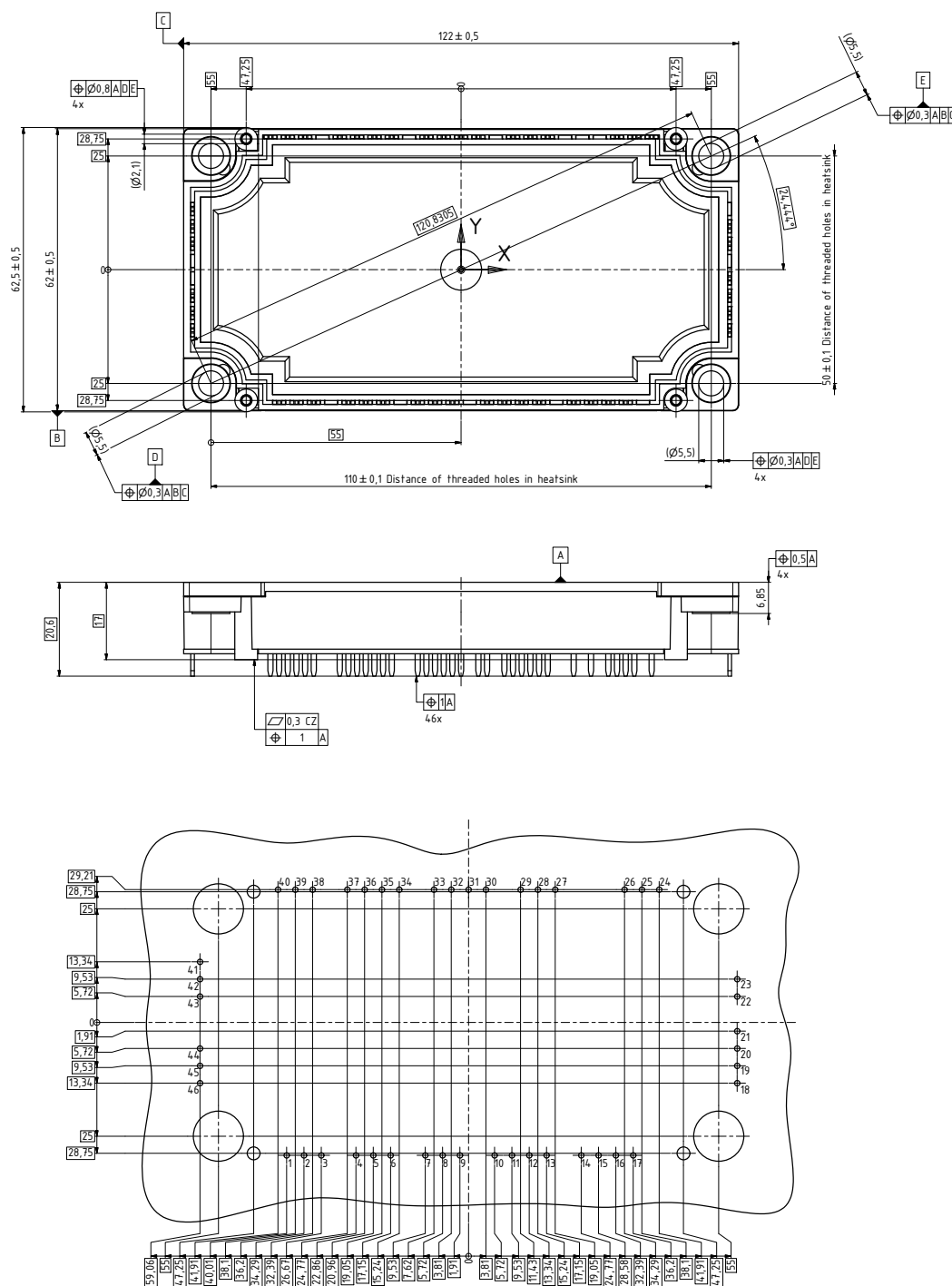


Figure 1

10 Package outlines



For PressFIT pin: Details about hole specification for contacts refer to AN2007-09
For Solderpin: Details about hole specification for contacts refer to AN2017-03

Recommended tolerance of threaded holes in heatsink ± 0.1 mm.
Dimensions according to ISO 14405 (G6) (Method of least squares (LSQ)).
Reference D and E defined with (G6)
ISO 8015 - Independency principle

W0021389.00

Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-11-12	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.10	2021-04-13	Preliminary datasheet
1.00	2022-07-13	Final datasheet

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